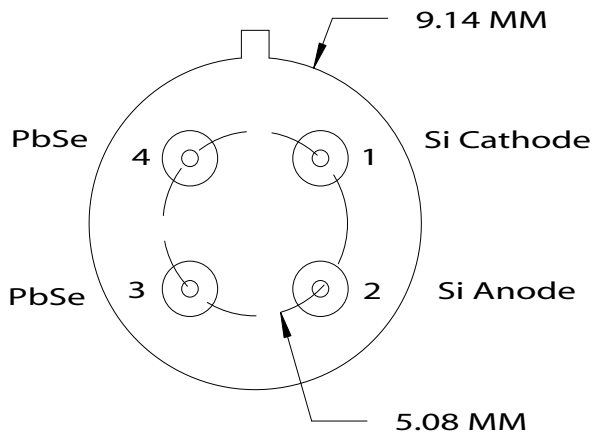


Si SPECIFICATIONS

TOP Si PV PHOTODIODE
 ACTIVE AREA - 2.5 MM
 WAVELENGTH - .3 - 1.0 Microns
 SHUNT RESISTANCE - 500 Mohms (min) @ 0V
 SHUNT CAPACITANCE - 400pF (typ)
 RESPONSIVITY - 0.55A/W @ 850nm
 $NEP(W/Hz^{1/2}) < 1 \times 10^{-14}$ @ 850nm
 TIME CONSTANT - 15us @ 0V



PbSe SPECIFICATIONS

BOTTOM PbSe PC DETECTOR
 ACTIVE AREA - 2MM X 2MM
 WAVELENGTH - 1.0 - 4.7 Microns
 RESISTANCE - .3-1.5 M ohms
 RESPONSIVITY - $> 3000V/W$
 $D^*(Pk,1000,1) \times 10^9 - 2.0$
 TIME CONSTANT - 3us

NOTE:

- All TO5 assemblies are hermetically sealed and leak tested
- Custom filters are available
- Other active areas and packages are available
- PbS, Ge and InGaAs materials are available

DO NOT SCALE DRAWING	DRAWN		DATE	N.E.P. NEW ENGLAND PHOTOCONDUCTOR				
	CHECKED		DATE					
	DESIGNER	GG	DATE	FS-2/2.5-5 2 COLOR				
	ENGINEER	PB	DATE					
MATERIAL:	PROJECT ENGINEER		DATE	A	CODE IDENT. NO.	TYPE	1489	REV
FINISH SPECS:	PROJECT APPROVAL		DATE					
	PMB 3/3/09			SCALE	none	SHEET	1	